

DATA SHEET

BFQ68

NPN 4 GHz wideband transistor

Product specification
File under Discrete Semiconductors, SC14

September 1995

NPN 4 GHz wideband transistor

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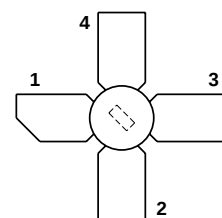
DESCRIPTION

NPN transistor mounted in a four-lead dual-emitter SOT122A envelope with a ceramic cap. All leads are isolated from the stud. Diffused emitter-ballasting resistors and the application of gold sandwich metallization ensure an optimum temperature profile and excellent reliability properties. It features very high output voltage capabilities.

It is primarily intended for final stages in MATV system amplifiers, and is also suitable for use in low power band IV and V equipment.

PINNING

PIN	DESCRIPTION
1	collector
2	emitter
3	base
4	emitter



Top view MBK187

Fig.1 SOT122A.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
V_{CEO}	collector-emitter voltage	open base	—	18	V
I_C	collector current		—	300	mA
P_{tot}	total power dissipation	up to $T_c = 110\text{ °C}$	—	4.5	W
f_T	transition frequency	$I_C = 240\text{ mA}$; $V_{CE} = 15\text{ V}$; $f = 500\text{ MHz}$; $T_j = 25\text{ °C}$	4	—	GHz
V_o	output voltage	$I_C = 240\text{ mA}$; $V_{CE} = 15\text{ V}$; $d_{im} = -60\text{ dB}$; $R_L = 75\text{ }\Omega$; $f_{(p+q-r)} = 793.25\text{ MHz}$; $T_{amb} = 25\text{ °C}$	1.6	—	V
P_{L1}	output power at 1 dB gain compression	$I_C = 240\text{ mA}$; $V_{CE} = 15\text{ V}$; $R_L = 75\text{ }\Omega$; $f = 800\text{ MHz}$; $T_{amb} = 25\text{ °C}$	28	—	dBm
ITO	third order intercept point	$I_C = 240\text{ mA}$; $V_{CE} = 15\text{ V}$; $R_L = 75\text{ }\Omega$; $f = 800\text{ MHz}$; $T_{amb} = 25\text{ °C}$	47	—	dBm

WARNING

Product and environmental safety - toxic materials

This product contains beryllium oxide. The product is entirely safe provided that the BeO disc is not damaged. All persons who handle, use or dispose of this product should be aware of its nature and of the necessary safety precautions. After use, dispose of as chemical or special waste according to the regulations applying at the location of the user. It must never be thrown out with the general or domestic waste.

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In accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	–	25	V
V _{CEO}	collector-emitter voltage	open base	–	18	V
V _{EBO}	emitter-base voltage	open collector	–	2	V
I _C	DC collector current		–	300	mA
P _{tot}	total power dissipation	up to T _C = 110 °C	–	4.5	W
T _{stg}	storage temperature		–65	150	°C
T _j	junction temperature		–	200	°C

THERMAL RESISTANCE

SYMBOL	PARAMETER	THERMAL RESISTANCE
R _{th j-c}	thermal resistance from junction to case	20 K/W

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CHARACTERISTICS

 $T_j = 25\text{ °C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CBO}	collector cut-off current	$I_E = 0$; $V_{CB} = 15\text{ V}$	–	–	50	μA
h_{FE}	DC current gain	$I_C = 240\text{ mA}$; $V_{CE} = 15\text{ V}$	25	75	–	
f_T	transition frequency	$I_C = 240\text{ mA}$; $V_{CE} = 15\text{ V}$; $f = 500\text{ MHz}$	–	4	–	GHz
C_c	collector capacitance	$I_E = I_E = 0$; $V_{CB} = 15\text{ V}$; $f = 1\text{ MHz}$	–	3.8	–	pF
C_e	emitter capacitance	$I_C = I_C = 0$; $V_{EB} = 0.5\text{ V}$; $f = 1\text{ MHz}$	–	20	–	pF
C_{re}	feedback capacitance	$I_C = 0$; $V_{CE} = 15\text{ V}$; $f = 1\text{ MHz}$	–	2.3	–	pF
C_{cs}	collector-stud capacitance	note 1	–	0.8	–	pF
G_{UM}	maximum unilateral power gain (note 2)	$I_C = 240\text{ mA}$; $V_{CE} = 15\text{ V}$; $f = 800\text{ MHz}$; $T_{amb} = 25\text{ °C}$	–	13	–	dB
V_o	output voltage	note 3	–	1.6	–	V
P_{L1}	output power at 1 dB gain compression (see Fig.2)	$I_C = 240\text{ mA}$; $V_{CE} = 15\text{ V}$; $R_L = 75\text{ }\Omega$; $T_{amb} = 25\text{ °C}$; measured at $f = 800\text{ MHz}$	–	28	–	dBm
ITO	third order intercept point (see Fig.2)	note 4	–	47	–	dBm

Notes

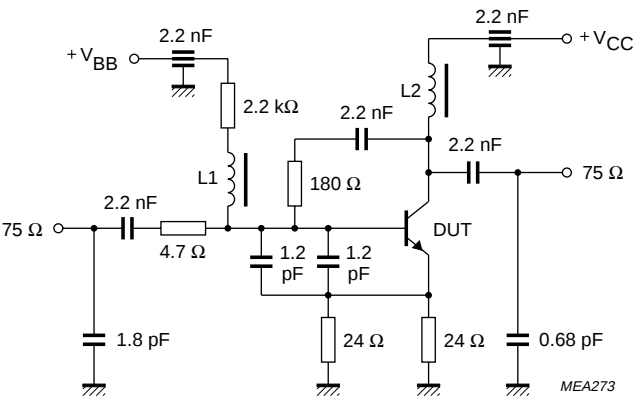
1. Measured with emitter and base grounded.
2. G_{UM} is the maximum unilateral power gain, assuming S_{12} is zero and

$$G_{UM} = 10 \log \left(\frac{|S_{21}|^2}{(1 - |S_{11}|^2)(1 - |S_{22}|^2)} \right) \text{ dB.}$$

3. $d_{im} = -60\text{ dB}$ (see Figs 2 and 7) (DIN 45004B); $I_C = 240\text{ mA}$; $V_{CE} = 15\text{ V}$; $R_L = 75\text{ }\Omega$; $T_{amb} = 25\text{ °C}$;
 $V_p = V_o$ at $d_{im} = -60\text{ dB}$; $f_p = 795.25\text{ MHz}$;
 $V_q = V_o - 6\text{ dB}$; $f_q = 803.25\text{ MHz}$;
 $V_r = V_o - 6\text{ dB}$; $f_r = 805.25\text{ MHz}$;
measured at $f_{(p+q-r)} = 793.25\text{ MHz}$.
4. $I_C = 240\text{ mA}$; $V_{CE} = 15\text{ V}$; $R_L = 75\text{ }\Omega$; $T_{amb} = 25\text{ °C}$;
 $P_p = \text{ITO} - 6\text{ dB}$; $f_p = 800\text{ MHz}$;
 $P_q = \text{ITO} - 6\text{ dB}$; $f_q = 801\text{ MHz}$;
measured at $f_{(2q-p)} = 802\text{ MHz}$ and at $f_{(2p-q)} = 799\text{ MHz}$.

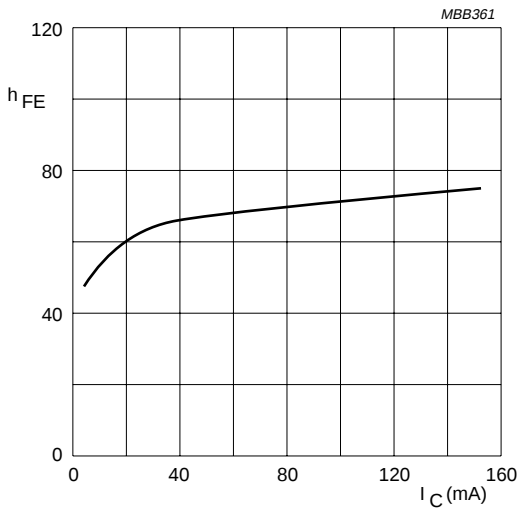
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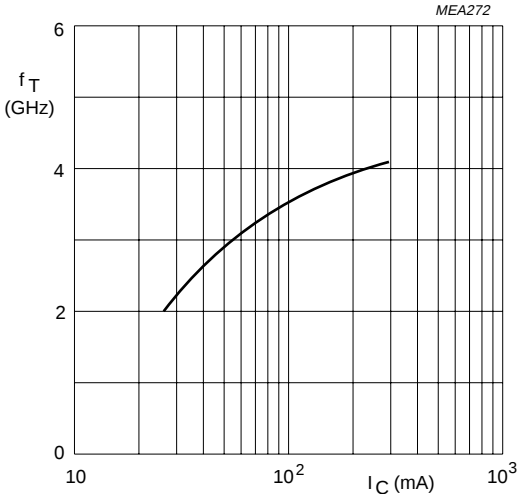
f = 40 to 860 MHz.
L1 = L2 = 5 μH Ferroxcube choke.

Fig.2 Intermodulation distortion MATV test circuit.



V_{CE} = 10 V; T_j = 25 °C.

Fig.3 DC current gain as a function of collector current.

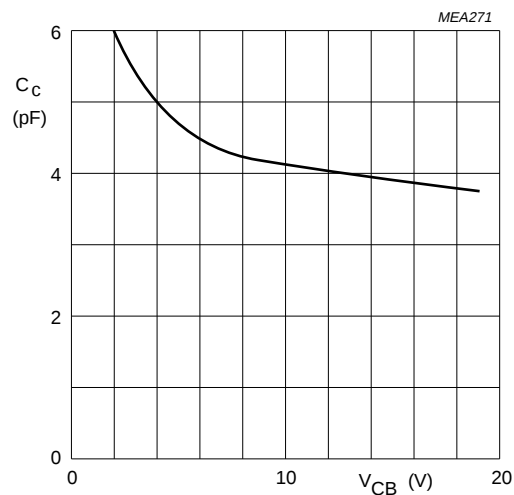


V_{CE} = 15 V; f = 500 MHz; T_j = 25 °C

Fig.4 Transition frequency as a function of collector current.

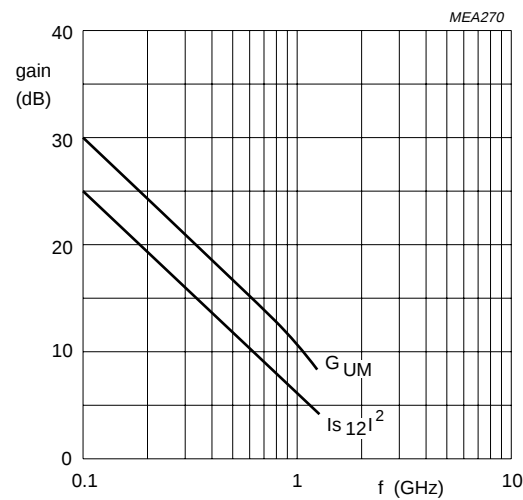
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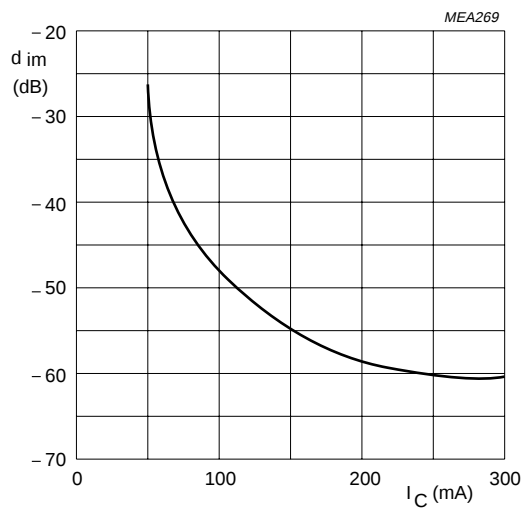
$I_E = i_e = 0$; $f = 1$ MHz

Fig.5 Collector capacitance as a function of collector-base voltage.



$I_C = 240$ mA; $V_{CE} = 15$ V; $T_{amb} = 25$ °C

Fig.6 Gain as a function of frequency.

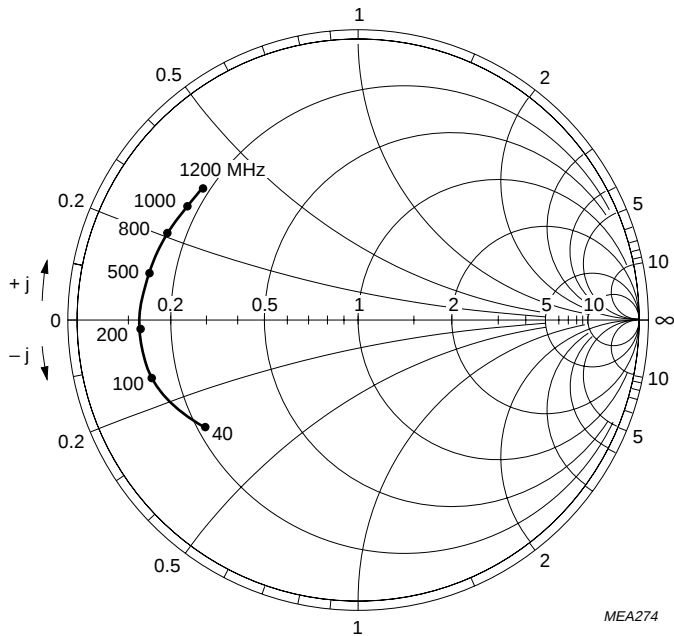


$V_{CE} = 15$ V; $V_0 = 1.6$ V; $f_{(p+q-r)} = 793.25$ MHz.

Fig.7 Intermodulation distortion as a function of collector current.

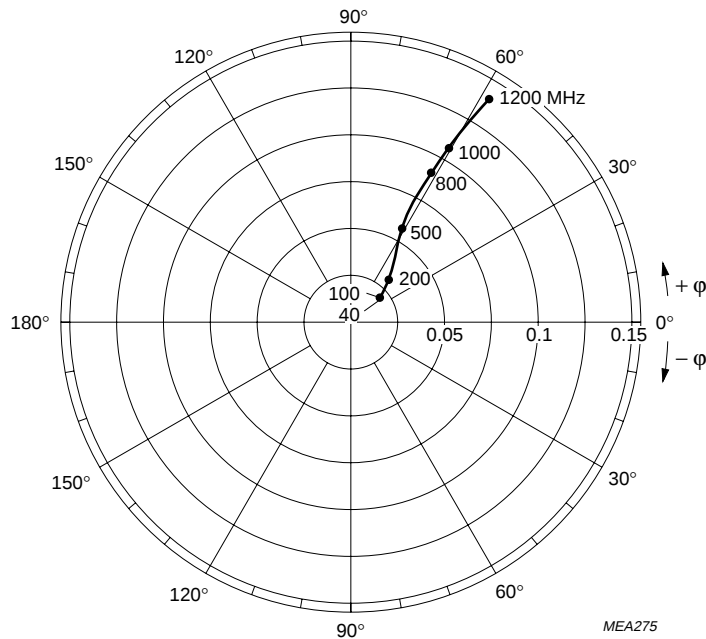
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$I_C = 240\text{ mA}$; $V_{CE} = 15\text{ V}$; $T_{amb} = 25\text{ }^\circ\text{C}$.
 $Z_0 = 50\text{ }\Omega$.

Fig.8 Common emitter input reflection coefficient (S_{11}).

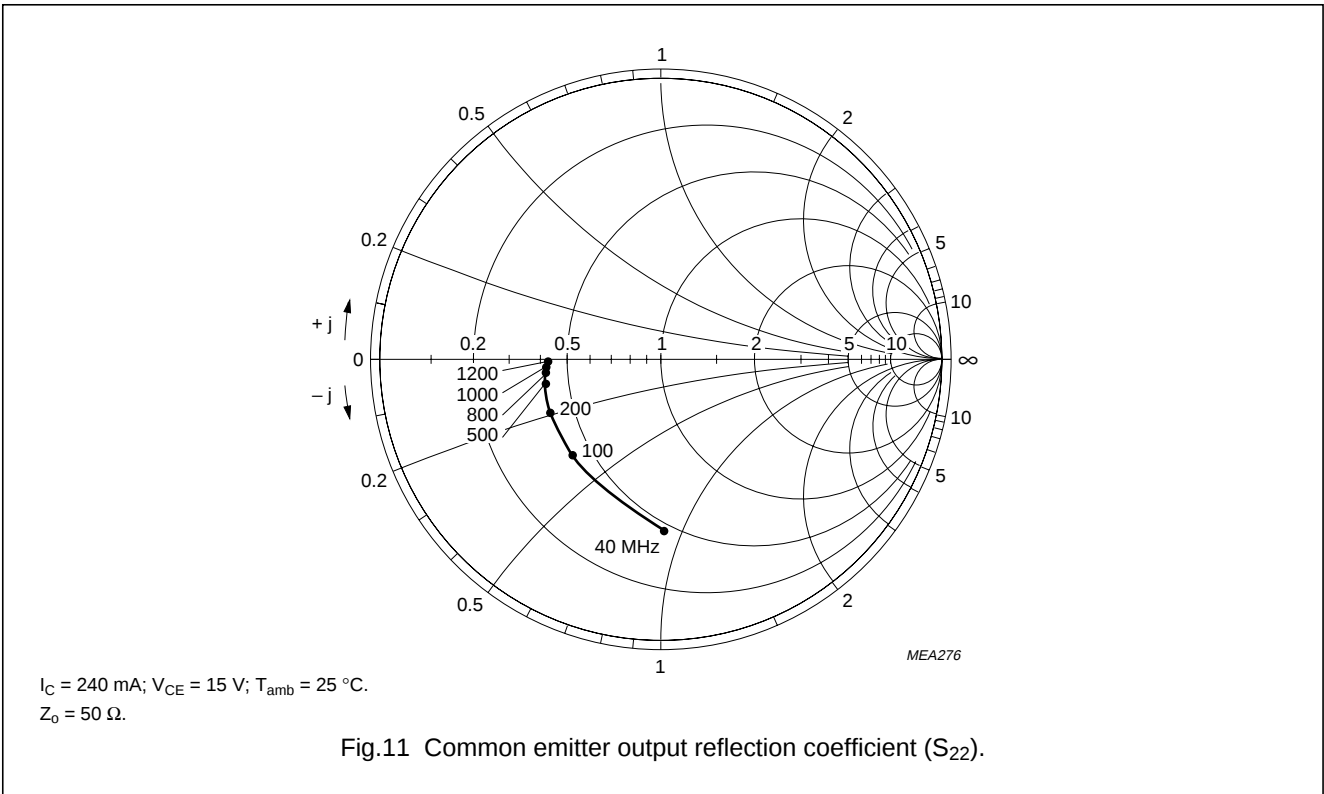
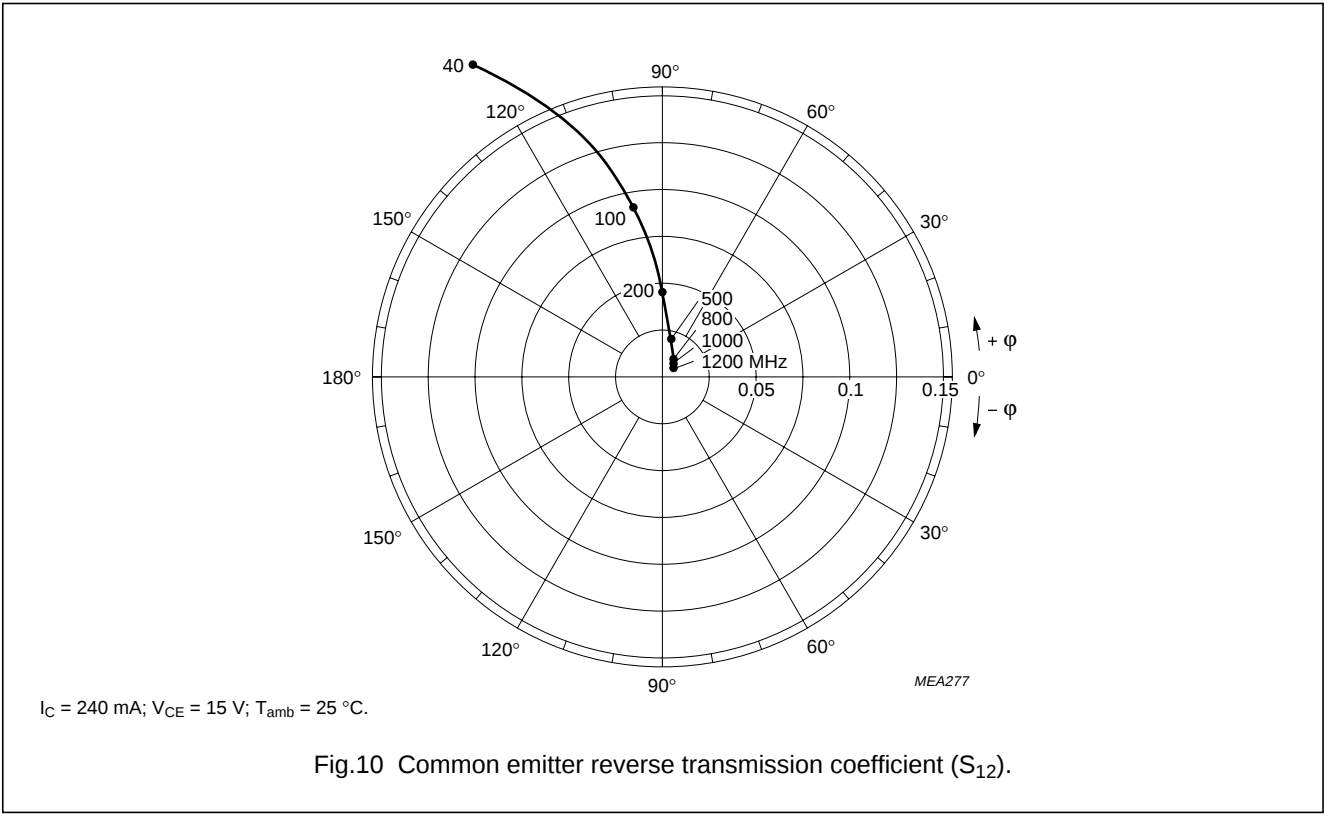


$I_C = 240\text{ mA}$; $V_{CE} = 15\text{ V}$; $T_{amb} = 25\text{ }^\circ\text{C}$.

Fig.9 Common emitter forward transmission coefficient (S_{21}).

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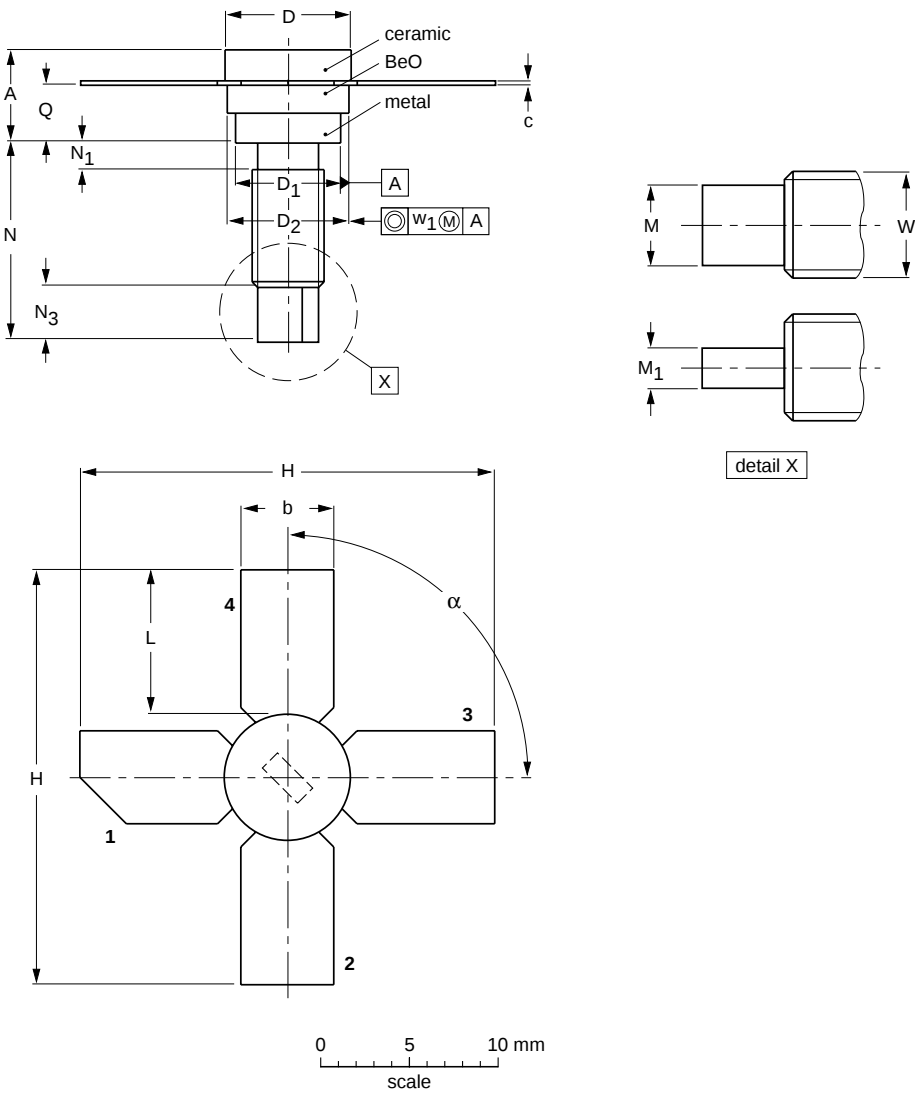
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PACKAGE OUTLINE

Studded ceramic package; 4 leads

SOT122A



DIMENSIONS (millimetre dimensions are derived from the original inch dimensions)

UNIT	A	b	c	D	D ₁	D ₂	H	L	M ₁	M	N	N ₁ max.	N ₃	Q	W	w ₁	α
mm	5.97 4.74	5.85 5.58	0.18 0.14	7.50 7.23	6.48 6.22	7.24 6.93	27.56 25.78	9.91 9.14	3.18 2.66	1.66 1.39	11.82 11.04	1.02	3.86 2.92	3.38 2.74	8-32 UNC	0.381	90°

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT122A						97-04-18

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DEFINITIONS

Data Sheet Status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
Application information	
Where application information is given, it is advisory and does not form part of the specification.	

LIFE SUPPORT APPLICATIONS

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